查询BC807供应商

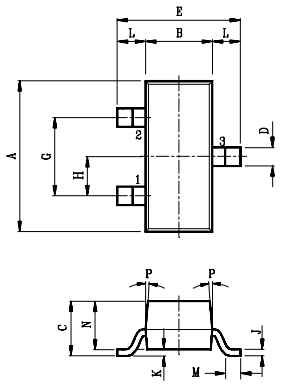
KOREA ELECTRONICS CO.,LTD.

SEMICONDUCTOR
TECHNICAL DATA

BC807
EPITAXIAL PLANAR PNP TRANSISTOR

GENERAL PURPOSE APPLICATION.
SWITCHING APPLICATION.

FEATURES
- Complementary to BC817.



DIM	MILLIMETERS
A	2.93±0.20
B	1.30+0.20/−0.15
C	1.30 MAX
D	0.45+0.15/−0.05
E	2.40+0.30/−0.20
G	1.90
H	0.95
J	0.13+0.10/−0.05
K	0.00 ~ 0.10
L	0.55
M	0.20 MIN
N	1.00+0.20/−0.10
P	7°

SOT-23

MAXIMUM RATINGS (Ta=25℃)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	-50	V
Collector-Emitter Voltage	V_{CEO}	-45	V
Emitter-Base Voltage	V_{EBO}	-5	V
Collector Current	I_C	-500	mA
Base Current	I_B	-100	mA
Collector Power Dissipation	P_C	150	mW
Junction Temperature	T_j	150	℃
Storage Temperature Range	T_{stg}	-55~150	℃

ELECTRICAL CHARACTERISTICS (Ta=25℃)

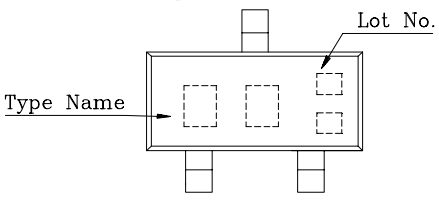
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CBO}	V_{CB}=-20V, I_E=0	-	-	-0.1	μA
Emitter Cut-off Current	I_{EBO}	V_{EB}=-5V, I_C=0	-	-	-0.1	μA
DC Current Gain (Note)	h_{FE}(1)	V_{CE}=-1V, I_C=-100mA	100	-	400	
	h_{FE}(2)	V_{CE}=-1V, I_C=-500mA	40	-	-	
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	I_C=-500mA, I_B=-50mA	-	-	-0.7	V
Base-Emitter Voltage	V_{BE}	V_{CE}=-1V, I_C=-500mA	-	-	-1.2	V
Transition Frequency	f_T	V_{CE}=-5V, I_C=-10mA, f=100MHz	80	-	-	MHz
Collector Output Capacitance	C_{ob}	V_{CB}=-10V, I_E=0, f=1MHz	-	9	-	pF

(Note) : h_{FE}(1) Classification 16:100~250 , 25:160~400

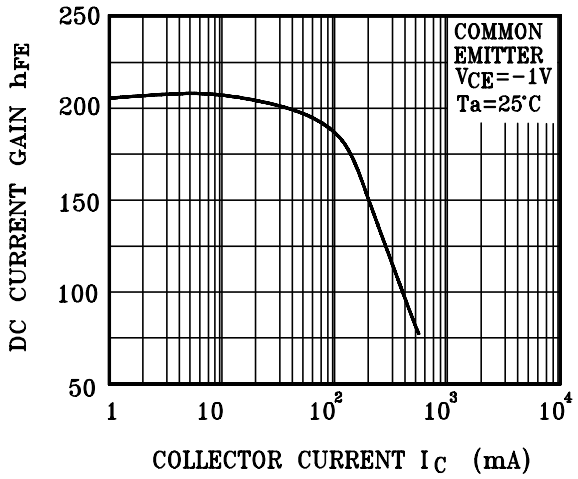
MARK SPEC

TYPE	BC807-16	BC807-25
MARK	5A	5B

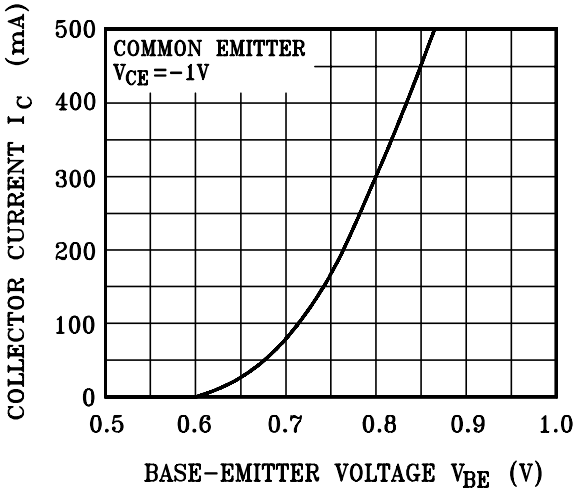
Marking



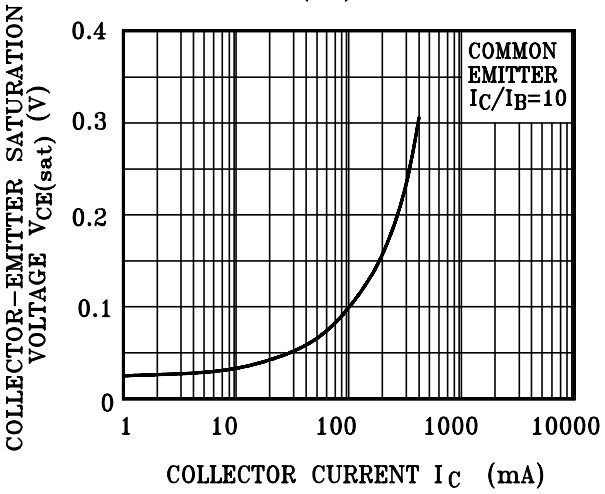
h_{FE} - I_C



I_C - V_{BE}



$V_{CE(sat)}$ - I_C



P_C - Ta